

# 5G\_GaN2

*Heterogeneous integration of state of the art  
Semiconductor Technology*

## Strategic Objective

5G\_GaN2 has as major objective to develop new industrial disruptive technologies from semiconductor to integration. It will support the birth of new sub system architectures and target the steps in performances for the 5G generation from Ku to E bands for BTS, point to point & SATCOM communication networks

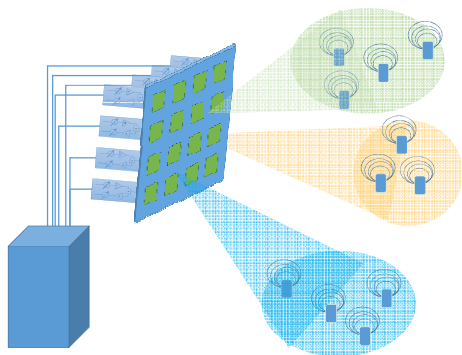


[www.5ggan2.eu](http://www.5ggan2.eu)

Start date:	1 June 2018
Duration:	36 months
Total costs:	21 M€
Number of participants:	17
Number of countries:	9
Project coordinator:	Philippe Auxemery

## 5G Telecom and Satcom Active Antenna System

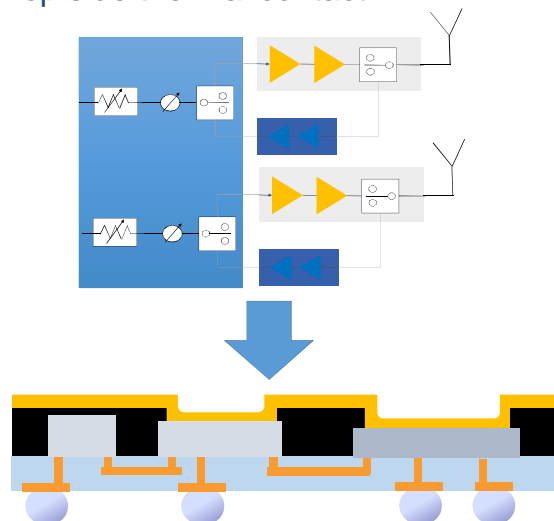
Phased antenna arrays are a vital part of the newly emerging 5G technologies. Thanks to the ability of beam-forming and beam-steering spatial diversity is achieved. The spatial diversification is reached by enabling control over the shape and direction of the antenna's radiation pattern.



The radiating elements of phased antenna arrays ought to be spaced by about  $0.5\lambda$ . At 30GHz, the mesh of the antenna is about 5mm, therefore transmit and receive RF components must be smaller than  $5 \times 5 \text{ mm}^2$

## Fan Out Wafer Level Packaging benefit

- High integration
  - Active and passive dies
  - Short interconnections
- Heterogeneous integration
  - Mix of state of the art technologies for RF and digital functions
- Top side thermal contact



## Advanced Semiconductor Power Technologies

- 0.15  $\mu\text{m}$  GaN on Si technology compatible of 8" inches CMOS line
- mmWave 0.08  $\mu\text{m}$  GaN on SiC power technology

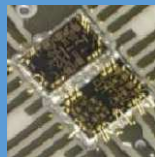
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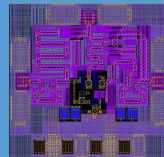
**0.15&0.1µm  
GaN Technology**



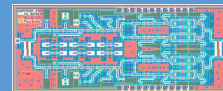
**5G RF Front End  
24-30GHz mixed  
GaN/GaAs**



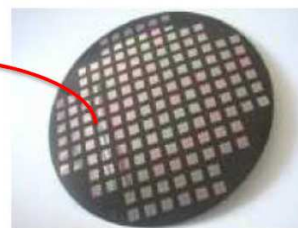
**39GHz RFSOI  
Switch**



**80GHz 2W GaN High  
Power Amplifier**



Compact RF Front End demonstrators covering 28, 39 and 80 GHz  
based on innovative Wafer Level Packaging integration



- 3D integration
- New system architecture
- Mixed of RF and digital functions



# YOUR PROJECT NAME

**BUCHAREST** **ECSEL JU**  
**SYMPOSIUM**  
June 17-18 2019

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